

TOSHIBA Transistor Silicon NPN Triple Diffused Type

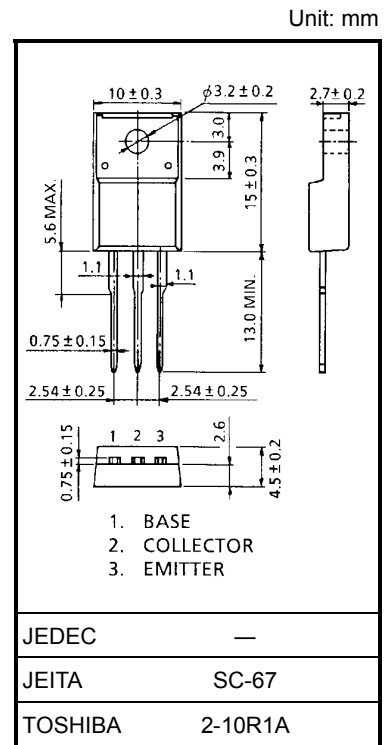
2SC5563

Dynamic Focus Applications

- High voltage: $V_{CE0} = 1500\text{ V}$
- Small collector output capacitance: $C_{ob} = 2.0\text{ pF (typ.)}$ ($V_{CB} = 100\text{ V}$)

Maximum Ratings ($T_c = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	1500	V
Collector-emitter voltage	V_{CEO}	1500	V
Emitter-base voltage	V_{EBO}	7	V
Collector current	DC	I_C	20
	Pulse	I_{CP}	40
Base current	I_B	10	mA
Collector power dissipation	$T_c = 25^\circ\text{C}$	P_C	10
	$T_a = 25^\circ\text{C}$		2
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$

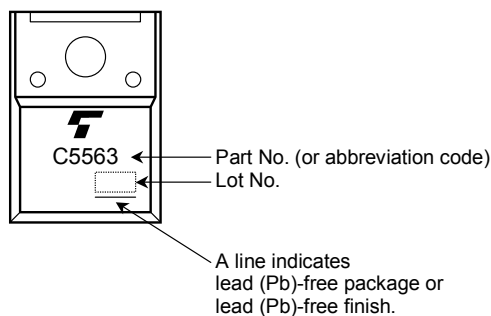


Weight: 1.7 g (typ.)

Electrical Characteristics ($T_c = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 1500\text{ V}, I_E = 0$	—	—	1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 7\text{ V}, I_C = 0$	—	—	10	μA
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 0.1\text{ mA}, I_E = 0$	1500	—	—	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{ mA}, I_B = 0$	1500	—	—	V
DC current gain	h_{FE}	$V_{CE} = 5\text{ V}, I_C = 1\text{ mA}$	10	—	60	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{ mA}, I_B = 2\text{ mA}$	—	—	5.0	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10\text{ mA}, I_B = 2\text{ mA}$	—	—	1.3	V
Collector output capacitance	C_{ob}	$V_{CB} = 100\text{ V}, f = 1\text{ MHz}, I_E = 0$	—	2.0	—	pF

Marking



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